

TSMC-02-210

January 22, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/714,304 11/14/03 |
Chao-Cheng Chen et al.
A NEW DUAL DAMASCENE PROCESS FLOW
FOR POROUS LOW-K MATERIALS
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

SB Ackerman 1/27/04

TSMC-02-210

U.S. Patent 6,350,681 to Chen et al., "Method of Forming Dual Damascene Structure," describes a dual damascene comprising an etch via and an etch trench.

U.S. Patent 6,291,887 to Wang et al., "Dual Damascene Arrangements for Metal Interconnection with Low K Dielectric Constant Materials and Nitride Middle Etch Stop Layer," describes a dual damascene with low-k layers comprising an etch via and an etch trench with a nitride middle etch stop layer.

U.S. Patent 6,287,955 to Wang et al., "Integrated Circuits with Multiple Low Dielectric-constant Inter-metal Dielectrics," describes a dual damascene with multiple low-k intermetal dielectric layers comprising an etch via and an etch trench.

U.S. Patent 6,300,235 to Feldner et al., "Method of Forming Multi-level Coplanar Metal/Insulator Films Using Dual Damascene with Sacrificial Flowable Oxide," describes a dual damascene with low-k layers comprising an etch via and an etch trench with sacrificial flowable oxide.

Sincerely,

A handwritten signature in black ink, appearing to read "SBA", with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

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10/714,304

Applicant

Chao-Chang Chen et al.

Filing Date

11/14/03

Group Art Unit

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

(Use several sheets if necessary)

U. S. PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
6350681	2/26/02	Chen et al.	438	637	2/9/01
6291887	9/18/01	Wang et al.	257	758	1/4/99
6287955	9/11/01	Wang et al.	438	623	11/22/00
6300235	10/9/01	Feldner et al.	438	618	6/30/97

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.